



Docket No.: M4065.0051/P051-A  
(PATENT)

#18/E  
Ext. 1740  
Dndt  
N/E

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

J. McInnis

In re Patent Application of:  
Leonard Forbes, et al.

Application No.: 09/609,813

Group Art Unit: 2815

Filed: July 3, 2000

Examiner: P. Brock, II

For: HIGH DENSITY PLANAR SRAM CELL  
USING BIPOLAR LATCHUP AND GATED  
DIODE BREAKDOWN

RECEIVED  
SEP 17 2002  
TECHNOLOGY CENTER 2800

**REQUEST FOR RECONSIDERATION  
AND AMENDMENT UNDER 37 C.F.R. § 1.116**

09/24/2002 JMC:115 00000003 041073 09609813  
Box Non-Fee Amendment  
Assistant Commissioner for Patents  
Washington, DC 20231  
110.00 CH

Dear Sir:

In response to the Office Action dated May 13, 2002 (Paper No. 17), please  
amend the above-identified U.S. Patent application as follows:

**In the Claims:**

**Please rewrite claims 48 and 55 as follows:**

48. (Thrice Amended) A method of forming a circuit for storing information as  
one of at least two possible stable current states, the method comprising the following  
steps:

providing a semiconductor substrate;

providing doped silicon regions to form a multi-region planar thyristor having at